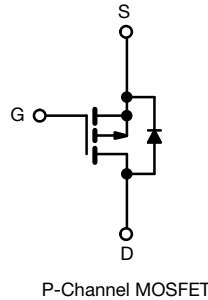
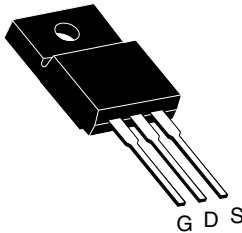


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	-60	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V	0.14
Q_g max. (nC)	34	
Q_{gs} (nC)	9.9	
Q_{gd} (nC)	16	
Configuration	Single	

TO-220 FULLPAK


FEATURES

- Isolated package
- High voltage isolation = 2.5 kV_{RMS} (t = 60 s; f = 60 Hz)
- Sink to lead creepage distance = 4.8 mm
- P-channel
- 175 °C operating temperature
- Dynamic dV/dt rating
- Low thermal resistance
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS*
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

DESCRIPTION

Third generation power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness. The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The molding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

ORDERING INFORMATION	
Package	TO-220 FULLPAK
Lead (Pb)-free	IRFI9Z34GPbF
	SiHFI9Z34G-E3
SnPb	IRFI9Z34G
	SiHFI9Z34G

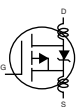

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL		LIMIT	UNIT
Drain-Source Voltage	V_{DS}		-60	V
Gate-Source Voltage	V_{GS}		± 20	
Continuous Drain Current	V_{GS} at -10 V	I_D	$T_C = 25$ °C	-12
			$T_C = 100$ °C	-8.5
Pulsed Drain Current ^a	I_{DM}		-48	A
Linear Derating Factor			0.28	
Single Pulse Avalanche Energy ^b	E_{AS}		370	mJ
Repetitive Avalanche Current ^a	I_{AR}		-12	A
Repetitive Avalanche Energy ^a	E_{AR}		4.2	mJ
Maximum Power Dissipation	$T_C = 25$ °C		P_D	42
Peak Diode Recovery dV/dt ^c	dV/dt		-4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}		-55 to +175	°C
Soldering Recommendations (Peak temperature) ^d	for 10 s		300	
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = -25$ V, starting $T_J = 25$ °C, L = 3.0 mH, $R_G = 25$ Ω , $I_{AS} = -12$ A (see fig. 12).
- $I_{SD} \leq -12$ A, $dI/dt \leq 170$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	3.6	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		-60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = -1\text{ mA}$		-	-0.060	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{ V}, V_{GS} = 0\text{ V}$		-	-	-100	μA
		$V_{DS} = -48\text{ V}, V_{GS} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -7.2\text{ A}^b$	-	-	0.14	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -25\text{ V}, I_D = -7.2\text{ A}^b$		5.4	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = -25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$		-	1100	-	pF
Output Capacitance	C_{oss}			-	620	-	
Reverse Transfer Capacitance	C_{rss}			-	100	-	
Drain to Sink Capacitance	C	$f = 1.0\text{ MHz}$		-	12	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}$	$I_D = -18\text{ A}, V_{DS} = -48\text{ V}, \text{ see fig. 6 and 13}^b$	-	-	34	nC
Gate-Source Charge	Q_{gs}			-	-	9.9	
Gate-Drain Charge	Q_{gd}			-	-	16	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -30\text{ V}, I_D = -18\text{ A}, R_G = 12\text{ }\Omega, R_D = 1.5\text{ }\Omega, \text{ see fig. 10}^b$		-	18	-	ns
Rise Time	t_r			-	120	-	
Turn-Off Delay Time	$t_{d(off)}$			-	20	-	
Fall Time	t_f			-	58	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 		-	4.5	-	nH
Internal Source Inductance	L_S			-	7.5	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz}, \text{ open drain}$		0.7	-	3.9	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p-n junction diode 		-	-	-12	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	-48	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -12\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	-6.3	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -18\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$		-	100	200	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	0.28	0.52	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

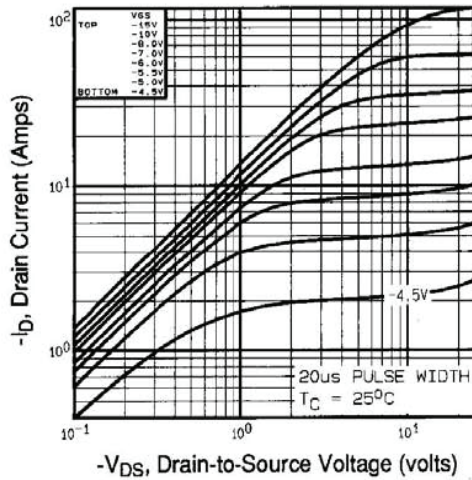


Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

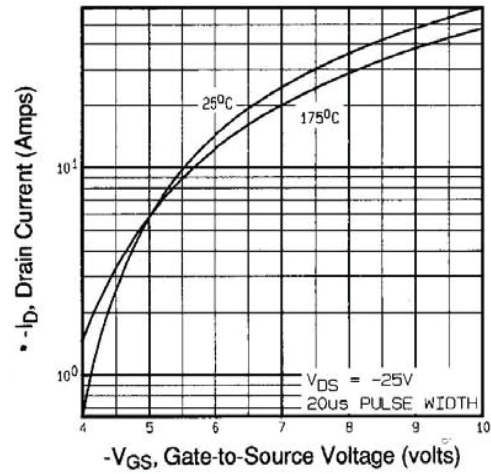


Fig. 3 - Typical Transfer Characteristics

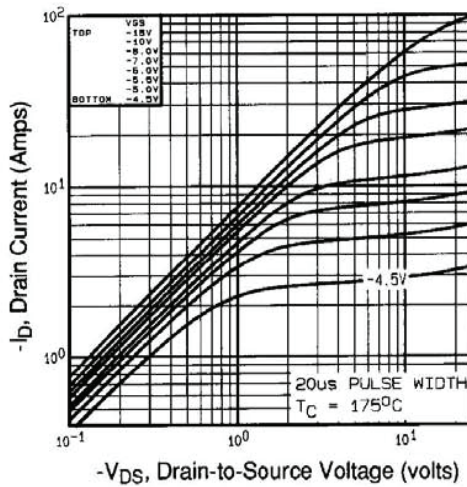


Fig. 2 - Typical Output Characteristics, $T_C = 175^\circ\text{C}$

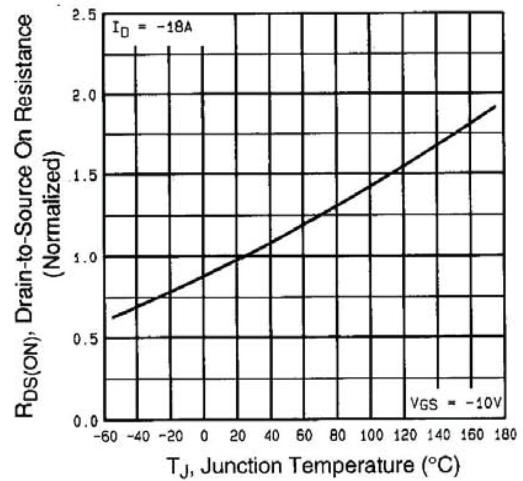


Fig. 4 - Normalized On-Resistance vs. Temperature

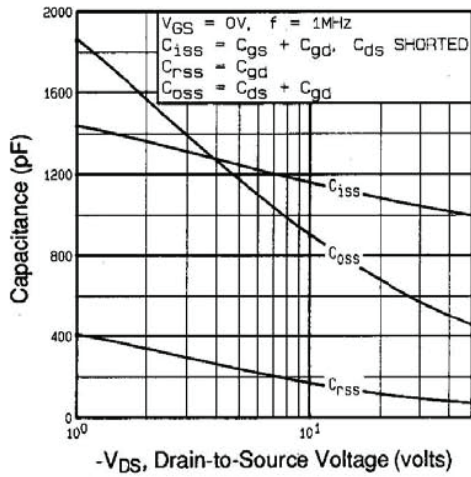


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

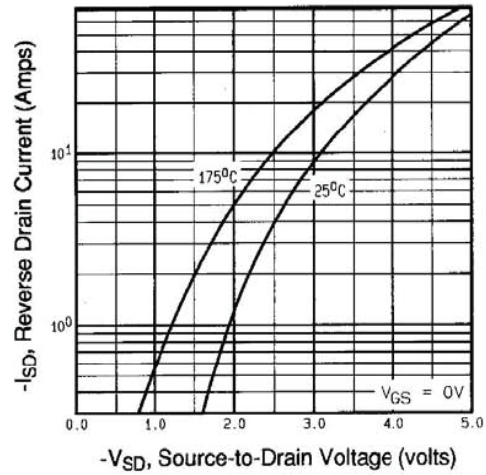


Fig. 7 - Typical Source-Drain Diode Forward Voltage

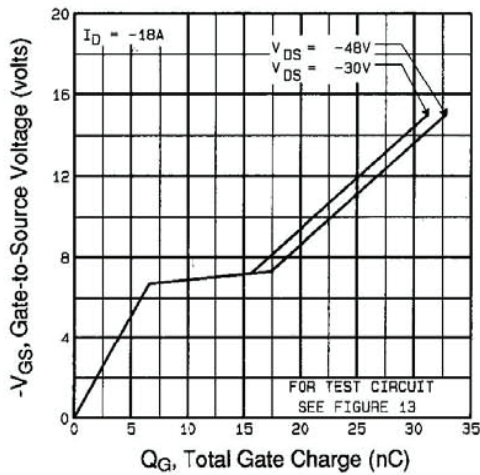


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

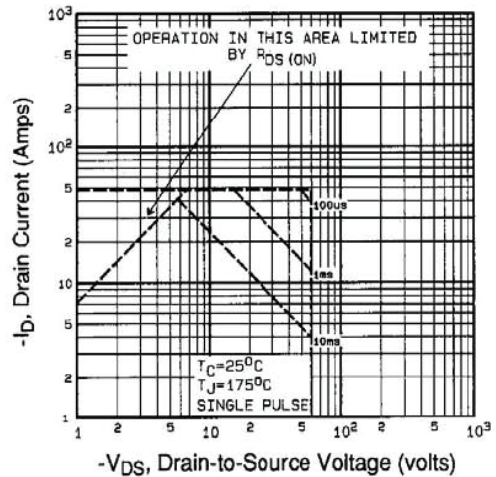


Fig. 8 - Maximum Safe Operating Area

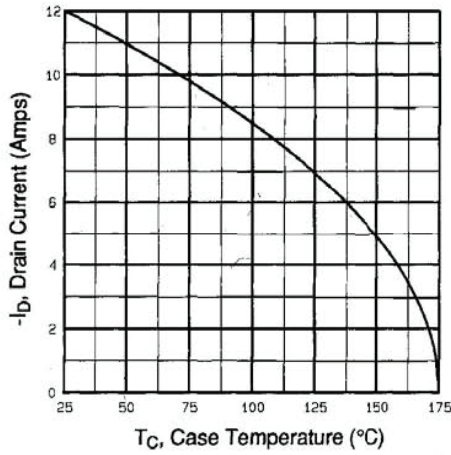


Fig. 9 - Maximum Drain Current vs. Case Temperature

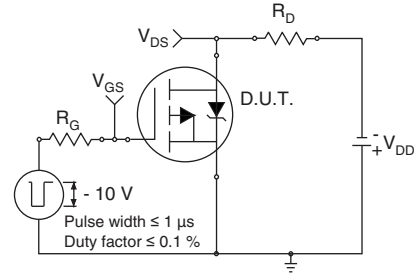


Fig. 10a - Switching Time Test Circuit

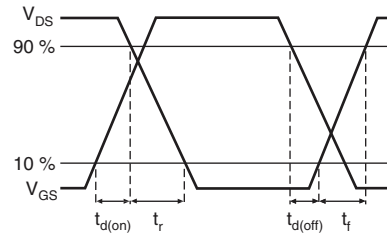


Fig. 10b - Switching Time Waveforms

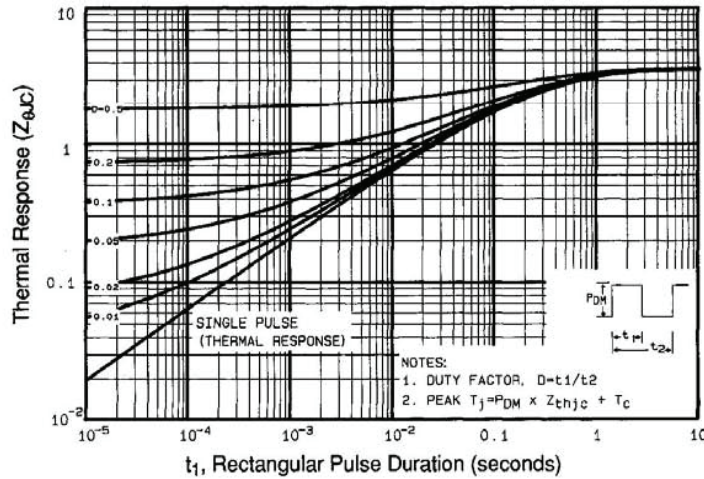


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

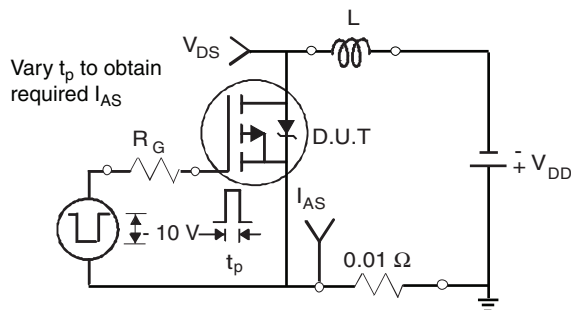


Fig. 12a - Unclamped Inductive Test Circuit

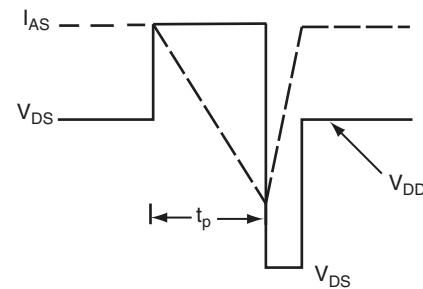


Fig. 12b - Unclamped Inductive Waveforms

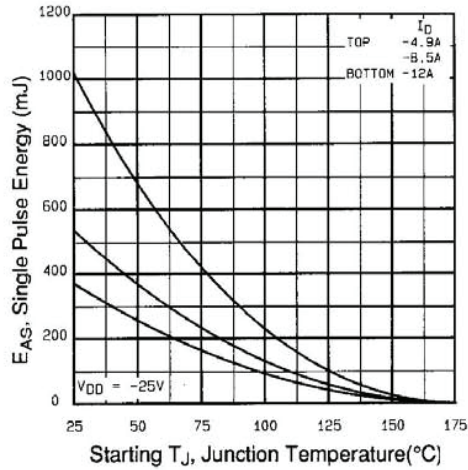


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

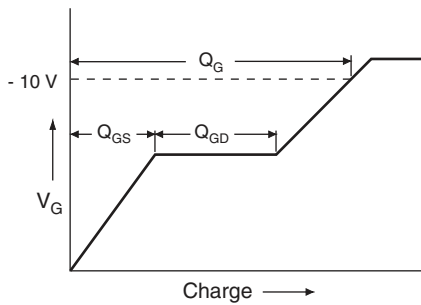


Fig. 13a - Basic Gate Charge Waveform

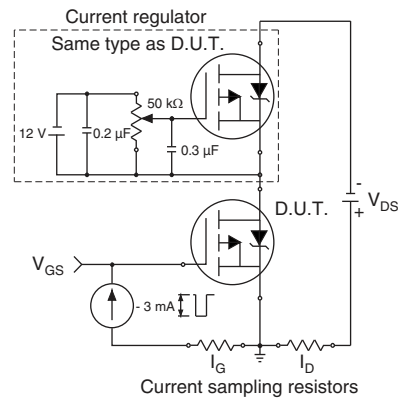


Fig. 13b - Gate Charge Test Circuit

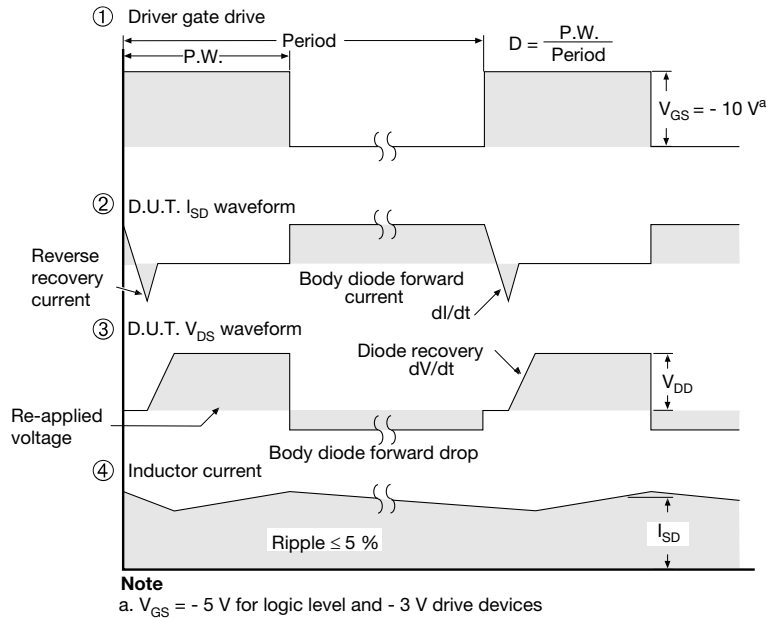
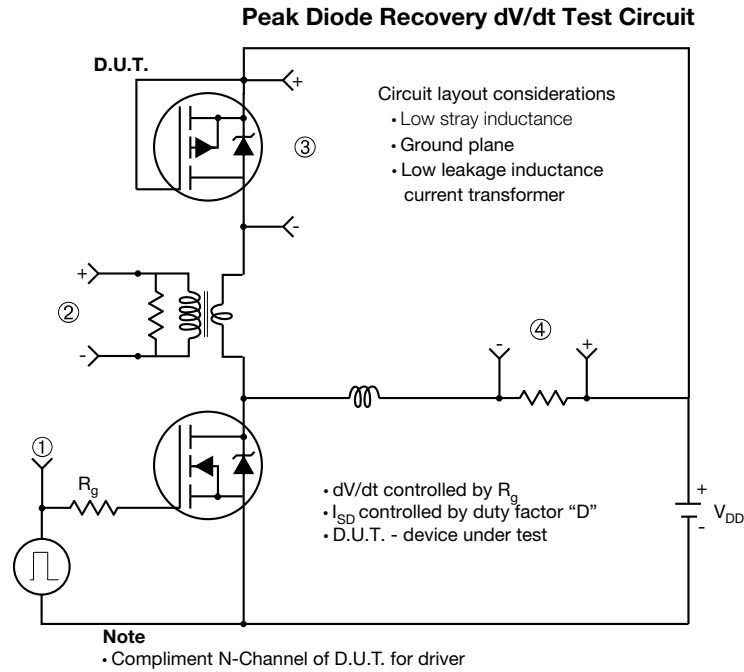


Fig. 14 - For P-Channel

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